

BF509**CASE 29-02, STYLE 17
TO-92 (TO-226AA)****VHF TRANSISTOR****PNP SILICON****MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CE0}	35	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current – Continuous	I_C	50	mA
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	Watt mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

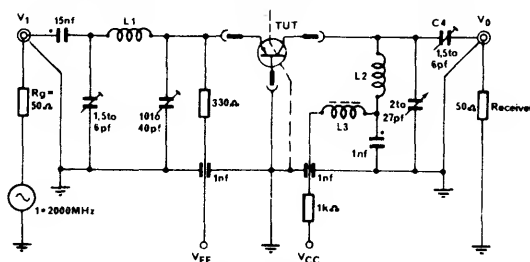
Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 5.0 \text{ mA}$, $I_E = 0$)	$V_{(BR)CE0}$	35	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	4	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20 \text{ V}$, $I_E = 0$)	I_{CBO}	—	—	100	nA

ON CHARACTERISTICS

DC Current Gain ($I_C = 3 \text{ mA}$, $V_{CE} = 10 \text{ Vdc}$)	h_{FE}	20	—	—	
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SMALL SIGNAL CHARACTERISTICS

Current-Gain – Bandwidth Product ($I_C = 3 \text{ mA}$, $V_{CE} = 10 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	600	850	—	MHz
Feedback Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{rb}	—	0.15	0.25	pF
Collector-Base Capacitance ($V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	$C_{CBO} (C_{re})$	—	0.6	0.9	pF
Noise Figure ($I_C = 3 \text{ mA}$, $V_{CC} = 10.8 \text{ V}$, $R_S = 50 \text{ Ohms}$, $f = 200 \text{ MHz}$)	N_F	—	—	2.5	dB
Common-Base Amplifier Power Gain ($I_C = 3 \text{ mA}$, $V_{CC} = 10.8 \text{ V}$, $R_L = 1 \text{ K}\Omega$, $f = 200 \text{ MHz}$)	G_{pb}	15	22	—	dB
Forward AGC Current ($I_C(\text{Agc})$ (Gain Reduction = 30 dB, $R_S = 50 \text{ Ohms}$, $V_{CC} = 10.8 \text{ V}$, $f = 200 \text{ MHz}$)	$I_C(\text{Agc})$	7	—	8.8	mA

200 MHz POWER GAIN NOISE FIGURE TEST CIRCUIT

*Leadless ceramic disc capacitor
 $L_1 = 3 \text{ turns, } 0.0 \text{ mm enamel, } 4 \text{ mm dia}$
 $L_2 = 2 \text{ turns } 1 \text{ mm enamel, } 6.5 \text{ mm dia}$

FIGURE 1 – DC CURRENT GAIN

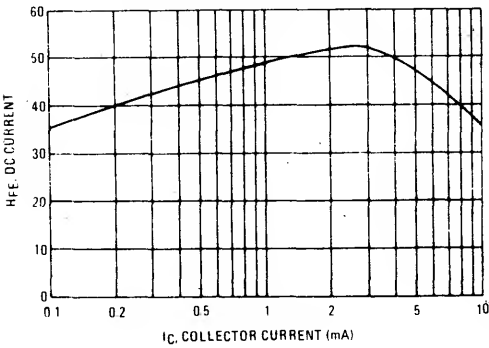
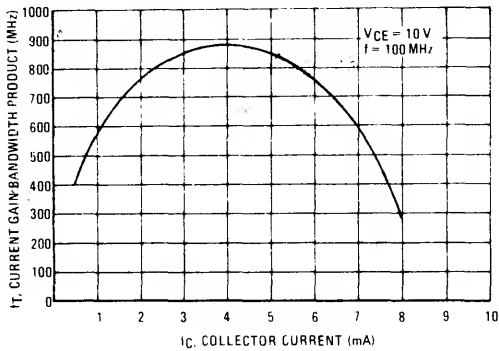


FIGURE 2 – CURRENT GAIN – BANDWIDTH PRODUCT



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FIGURE 3 – CAPACITANCES

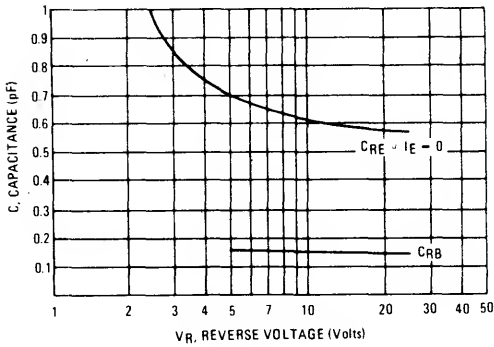


FIGURE 4 – TYPICAL POWER GAIN

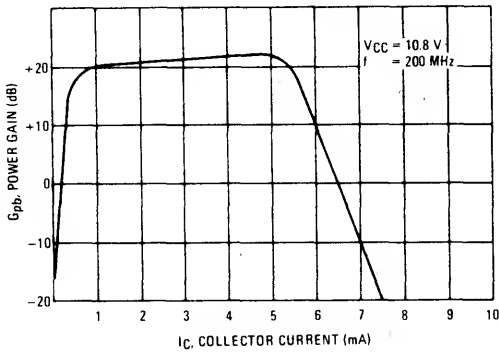


FIGURE 5 – FORWARD TRANSFER ADMITTANCE

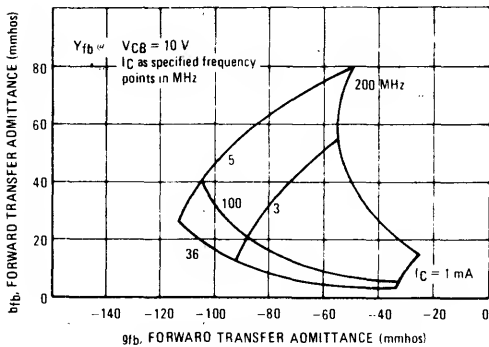


FIGURE 6 – INPUT ADMITTANCE

